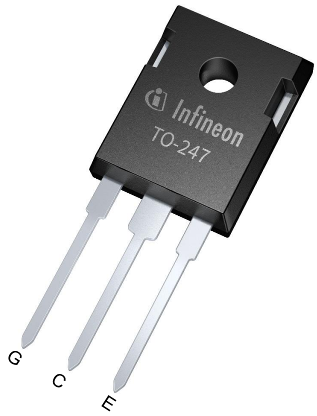
High speed 1200 V TRENCHSTOP™ IGBT 7 Technology co-packed with full rated current, soft-commutating, ultra-fast recovery and low Qrr emitter controlled 7 Rapid diode



Features

- V_{CE} = 1200 V
- I_C = 75 A
- Maximum junction temperature T_{vjmax} = 175°C
- Best-in-class high speed IGBT co-packed with full rated current, low Q_{rr} and soft-commutating high speed diode
- Low saturation voltage V_{CEsat} = 1.7 V at T_{vj} = 25°C
- Optimized for high efficiency in high speed hard switching topologies (2-L inverter, 3-L NPC T-type, ...)
- Easy paralleling capability due to positive temperature coefficient in V_{CEsat}
- Pb-free lead plating; RoHS compliant
- Complete product spectrum and PSpice Models: http://www.infineon.com/igbt/

Halogen-free
Lead-free
Green
RoHS

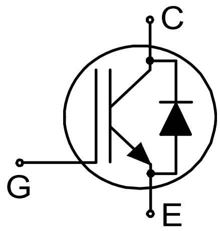
Potential applications

- Industrial UPS
- EV-Charging
- String inverter
- Welding

Product validation

- Qualified for industrial applications according to the relevant tests of JEDEC47/20/22

Description



Type	Package	Marking
IKW75N120CH7	PG-TO247-3-STD-NN2.5	K75MCH7

Table of contents

1 Package

Table 1 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Internal emitter inductance measured 5 mm (0.197 in.) from case	L_E			13		nH
Storage temperature	T_{stg}		-55		150	°C
Soldering temperature	T_{sold}	wave soldering 1.6 mm (0.063 in.) from case for 10 s			260	°C
Mounting torque	M	M3 screw, Maximum of mounting processes: 3			0.6	Nm
Thermal resistance, junction-ambient	$R_{th(j-a)}$				40	K/W
IGBT thermal resistance, junction-case	$R_{th(j-c)}$			0.21	0.27	K/W
Diode thermal resistance, junction-case	$R_{th(j-c)}$			0.36	0.47	K/W

2 IGBT

Table 2 Maximum rated values

Parameter	Symbol	Note or test condition		Values	Unit
Collector-emitter voltage	V_{CE}	$T_{vj} \geq 25$ °C		1200	V
DC collector current, limited by T_{vjmax}	I_C	limited by bondwire	$T_c = 25$ °C	92	A
			$T_c = 100$ °C	81	
Pulsed collector current, t_p limited by T_{vjmax}	I_{Cpulse}			300	A
Turn-off safe operating area		$V_{CC} \leq 800$ V, $V_{CE,peak} < 1200$ V, $V_{GE} = 0/15$ V, $R_{Goff} \geq 5.3\ \Omega$, $T_{vj} \leq 175$ °C		300	A
Gate-emitter voltage	V_{GE}			±20	V
Transient gate-emitter voltage	V_{GE}	$t_p \leq 0.5$ µs, $D < 0.001$		±25	V
Power dissipation	P_{tot}		$T_c = 25$ °C	549	W
			$T_c = 100$ °C	275	

Table 3 Characteristic values

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Collector-emitter saturation voltage	V_{CEsat}	I_C = 75 A, V_{GE} = 15 V	T_{vj} = 25 °C		1.7	2.15	V
			T_{vj} = 175 °C		2		
Gate-emitter threshold voltage	V_{GEth}	I_C = 1.2 mA, V_{CE} = V_{GE}		4.7	5.5	6.2	V
Zero gate-voltage collector current	I_{CES}	V_{CE} = 1200 V, V_{GE} = 0 V	T_{vj} = 25 °C			40	µA
			T_{vj} = 175 °C		4600		
Gate-emitter leakage current	I_{GES}	V_{CE} = 0 V, V_{GE} = 20 V				100	nA
Transconductance	g_{fs}	I_C = 75 A, V_{CE} = 20 V			123		S
Input capacitance	C_{ies}	V_{CE} = 25 V, V_{GE} = 0 V, f = 100 kHz			9.6		nF
Output capacitance	C_{oes}	V_{CE} = 25 V, V_{GE} = 0 V, f = 100 kHz			184		pF
Reverse transfer capacitance	C_{res}	V_{CE} = 25 V, V_{GE} = 0 V, f = 100 kHz			54		pF
Gate charge	Q_G	V_{CC} = 960 V, I_C = 75 A, V_{GE} = 15 V			535		nC
Turn-on delay time	$t_{d(on)}$	V_{CC} = 600 V, V_{GE} = 0/15 V, $R_{G(on)}$ = 8 Ω, $R_{G(off)}$ = 8 Ω	T_{vj} = 25 °C, I_C = 75 A		55		ns
			T_{vj} = 175 °C, I_C = 75 A		52		
Rise time (inductive load)	t_r	V_{CC} = 600 V, V_{GE} = 0/15 V, $R_{G(on)}$ = 8 Ω, $R_{G(off)}$ = 8 Ω	T_{vj} = 25 °C, I_C = 75 A		41		ns
			T_{vj} = 175 °C, I_C = 75 A		36		
Turn-off delay time	$t_{d(off)}$	V_{CC} = 600 V, V_{GE} = 0/15 V, $R_{G(on)}$ = 8 Ω, $R_{G(off)}$ = 8 Ω	T_{vj} = 25 °C, I_C = 75 A		461		ns
			T_{vj} = 175 °C, I_C = 75 A		527		
Fall time (inductive load)	t_f	V_{CC} = 600 V, V_{GE} = 0/15 V, $R_{G(on)}$ = 8 Ω, $R_{G(off)}$ = 8 Ω	T_{vj} = 25 °C, I_C = 75 A		32		ns
			T_{vj} = 175 °C, I_C = 75 A		97		
Turn-on energy	E_{on}	V_{CC} = 600 V, V_{GE} = 0/15 V, $R_{G(on)}$ = 8 Ω, $R_{G(off)}$ = 8 Ω	T_{vj} = 25 °C, I_C = 75 A		4.22		mJ
			T_{vj} = 175 °C, I_C = 75 A		5.86		

(table continues...)

Table 3 (continued) Characteristic values

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Turn-off energy	E_{off}	V_{CC} = 600 V, V_{GE} = 0/15 V, $R_{G(on)}$ = 8 Ω, $R_{G(off)}$ = 8 Ω	T_{vj} = 25 °C, I_C = 75 A		1.66		mJ
			T_{vj} = 175 °C, I_C = 75 A		3.37		
Total switching energy	E_{ts}	V_{CC} = 600 V, V_{GE} = 0/15 V, $R_{G(on)}$ = 8 Ω, $R_{G(off)}$ = 8 Ω	T_{vj} = 25 °C, I_C = 75 A		5.88		mJ
			T_{vj} = 175 °C, I_C = 75 A		9.23		
Operating junction temperature	T_{vj}			-40		175	°C

Note: Electrical Characteristic, at T_{vj} = 25°C, unless otherwise specified.

3 Diode

Table 4 Maximum rated values

Parameter	Symbol	Note or test condition		Values	Unit
Diode forward current, limited by T_{vjmax}	I_F	limited by bondwire	T_c = 25 °C	89	A
			T_c = 97 °C	75	
Diode pulsed current, t_p limited by T_{vjmax}	I_{Fpulse}			300	A
Power dissipation	P_{tot}		T_c = 25 °C	321	W
			T_c = 100 °C	160	

Table 5 Characteristic values

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Diode forward voltage	V_F	I_F = 75 A	T_{vj} = 25 °C		2.5	3	V
			T_{vj} = 175 °C		2.3		
Diode reverse recovery time	t_{rr}	V_R = 600 V, $R_{G(on)}$ = 8 Ω	T_{vj} = 25 °C, I_F = 75 A		145		ns
			T_{vj} = 175 °C, I_F = 75 A		218		
Diode reverse recovery charge	Q_{rr}	V_R = 600 V, $R_{G(on)}$ = 8 Ω	T_{vj} = 25 °C, I_F = 75 A		2.32		µC
			T_{vj} = 175 °C, I_F = 75 A		6.41		

(table continues...)

Table 5 (continued) Characteristic values

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Diode peak reverse recovery current	I_{rrm}	V_R = 600 V, $R_{G(on)}$ = 8 Ω	T_{vj} = 25 °C, I_F = 75 A		35		A
			T_{vj} = 175 °C, I_F = 75 A		62		
Diode peak rate of fall of reverse recovery current	di_{rr}/dt	V_R = 600 V, $R_{G(on)}$ = 8 Ω	T_{vj} = 25 °C, I_F = 75 A		-333		A/µs
			T_{vj} = 150 °C, I_F = 75 A		-394		
Reverse recovery energy	E_{rec}	V_R = 600 V, $R_{G(on)}$ = 8 Ω	T_{vj} = 25 °C, I_F = 75 A		0.701		mJ
			T_{vj} = 175 °C, I_F = 75 A		2.16		
Operating junction temperature	T_{vj}			-40		175	°C

Note: *For optimum lifetime and reliability, Infineon recommends operating conditions that do not exceed 80% of the maximum ratings stated in this datasheet.*

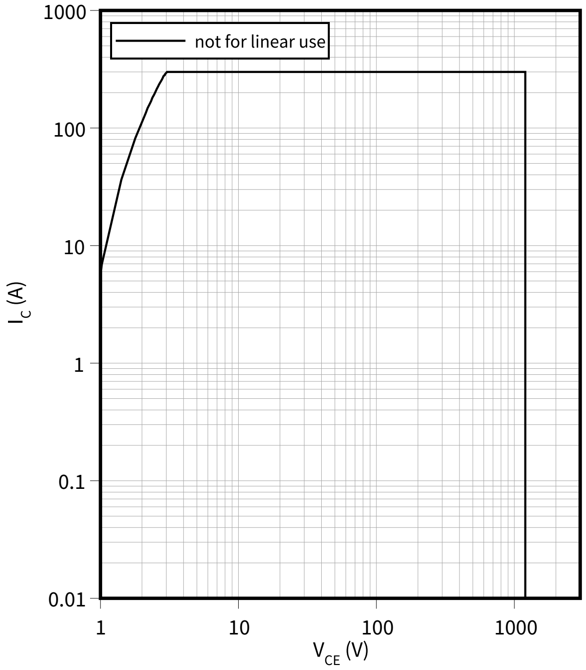
Dynamic test circuit, parasitic inductance L_σ = 30 nH, C_σ = 18 pF

4 Characteristics diagrams

Reverse bias safe operating area

$I_C = f(V_{CE})$

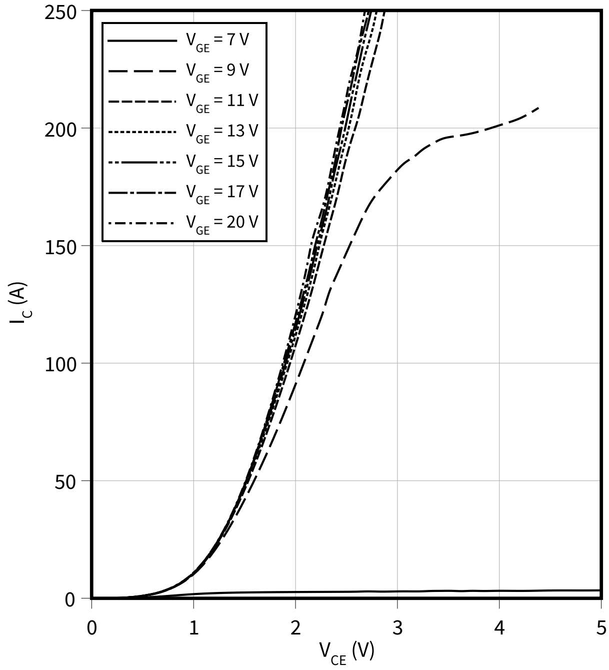
$T_{vj} \leq 175\ °C$, $V_{GE} = 0/15\ V$



Typical output characteristic

$I_C = f(V_{CE})$

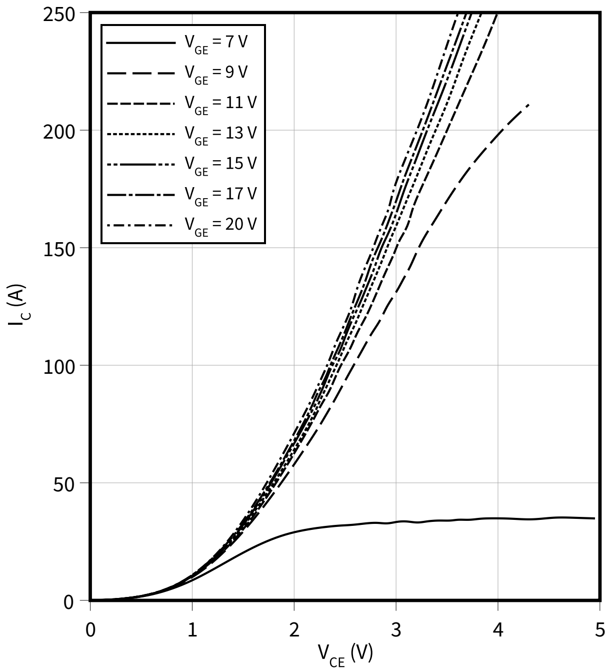
$T_{vj} = 25\ °C$



Typical output characteristic

$I_C = f(V_{CE})$

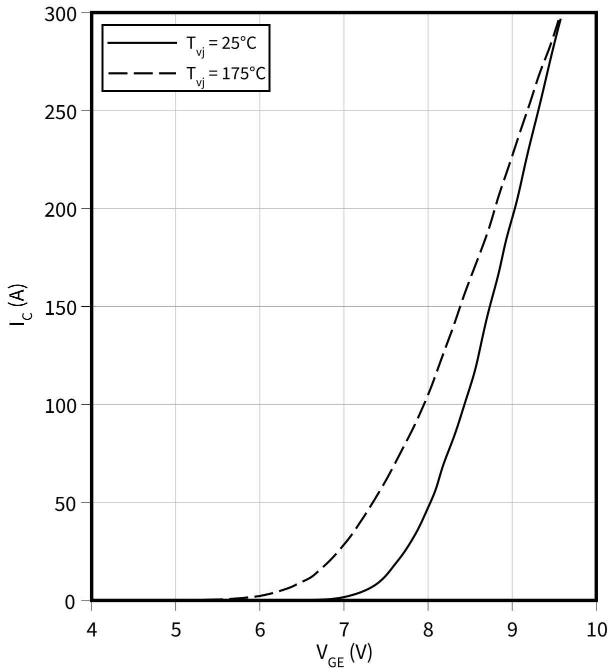
$T_{vj} = 175\ °C$



Typical transfer characteristic

$I_C = f(V_{GE})$

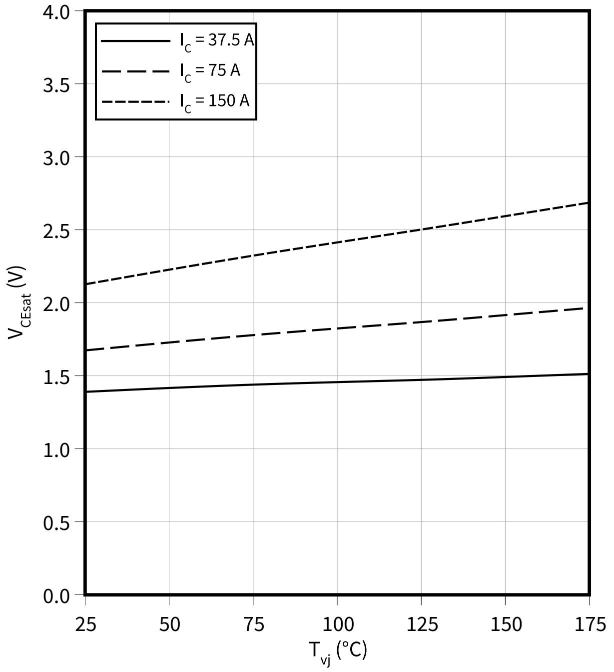
$V_{CE} = 20\ V$



Typical collector-emitter saturation voltage as a function of junction temperature

$V_{CEsat} = f(T_{vj})$

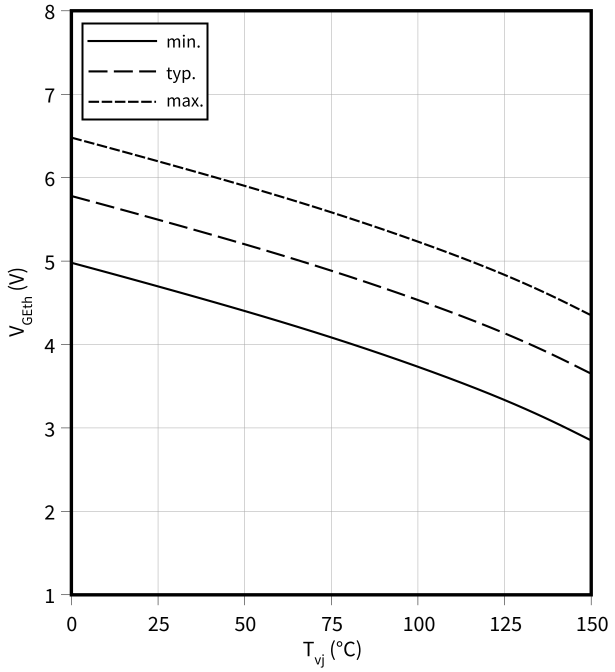
$V_{GE} = 15$ V



Gate-emitter threshold voltage as a function of junction temperature

$V_{GEth} = f(T_{vj})$

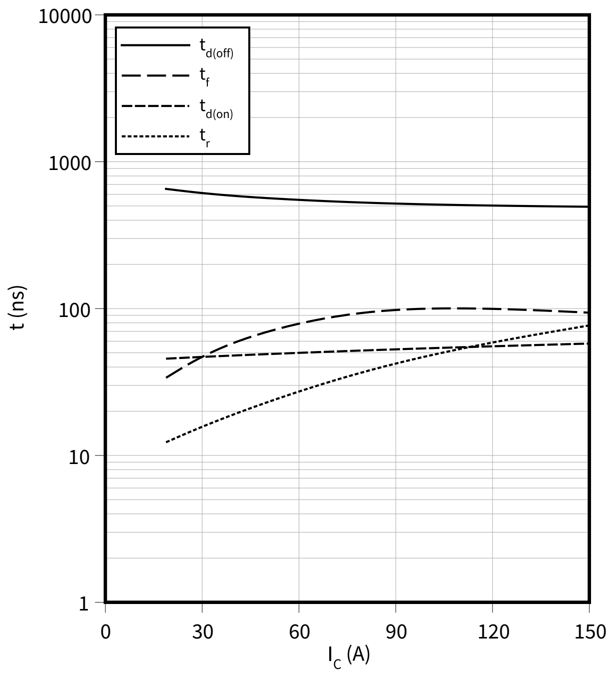
$I_C = 1.2$ mA



Typical switching times as a function of collector current

$t = f(I_C)$

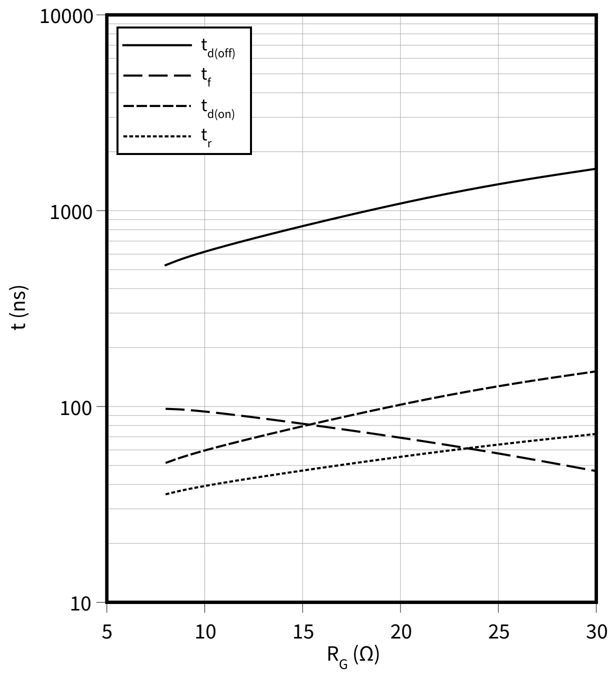
$V_{CC} = 600$ V, $T_{vj} = 175$ °C, $V_{GE} = 0/15$ V, $R_G = 8\ \Omega$



Typical switching times as a function of gate resistor

$t = f(R_G)$

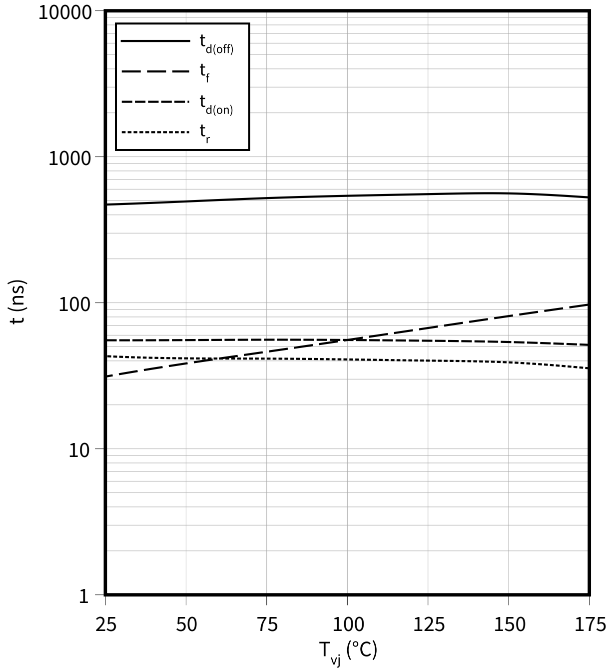
$I_C = 75$ A, $V_{CC} = 600$ V, $T_{vj} = 175$ °C, $V_{GE} = 0/15$ V



Typical switching times as a function of junction temperature

$t = f(T_{vj})$

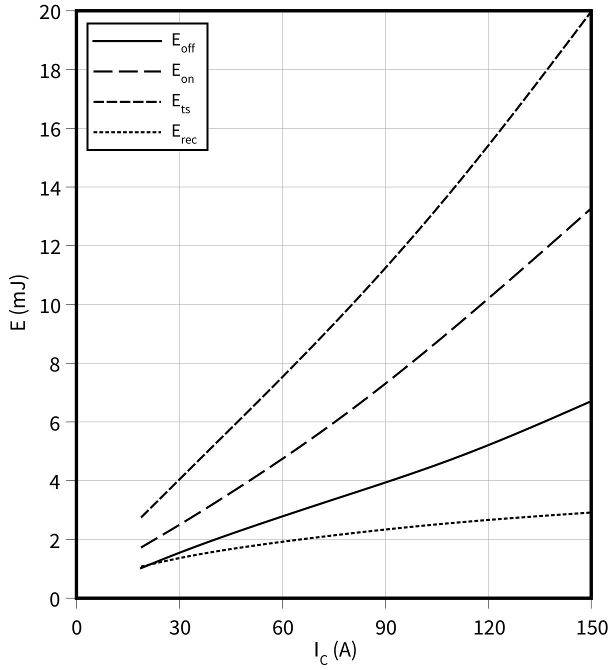
I_C = 75 A, V_{CC} = 600 V, V_{GE} = 0/15 V, R_G = 8 Ω



Typical switching energy losses as a function of collector current

$E = f(I_C)$

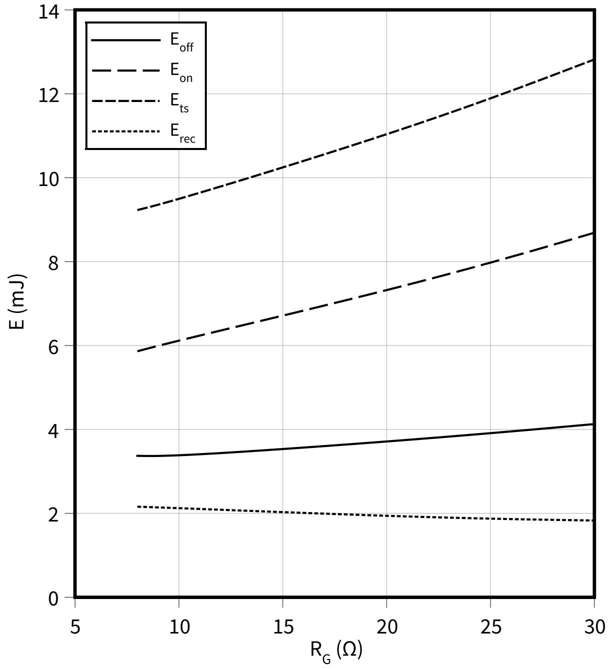
V_{CC} = 600 V, T_{vj} = 175 °C, V_{GE} = 0/15 V, R_G = 8 Ω



Typical switching energy losses as a function of gate resistor

$E = f(R_G)$

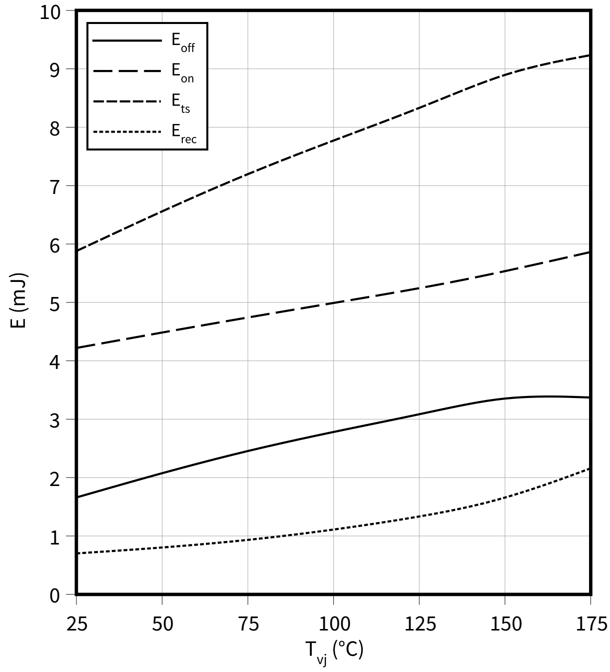
I_C = 75 A, V_{CC} = 600 V, T_{vj} = 175 °C, V_{GE} = 0/15 V



Typical switching energy losses as a function of junction temperature

$E = f(T_{vj})$

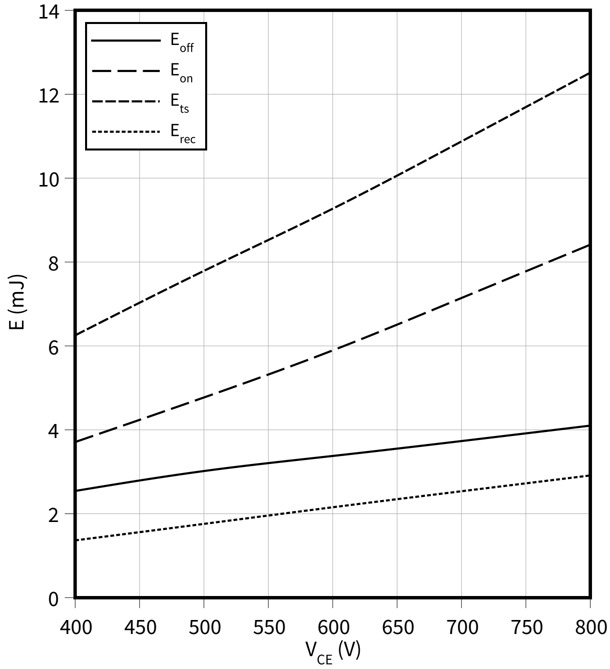
I_C = 75 A, V_{CC} = 600 V, V_{GE} = 0/15 V, R_G = 8 Ω



Typical switching energy losses as a function of collector emitter voltage

$E = f(V_{CE})$

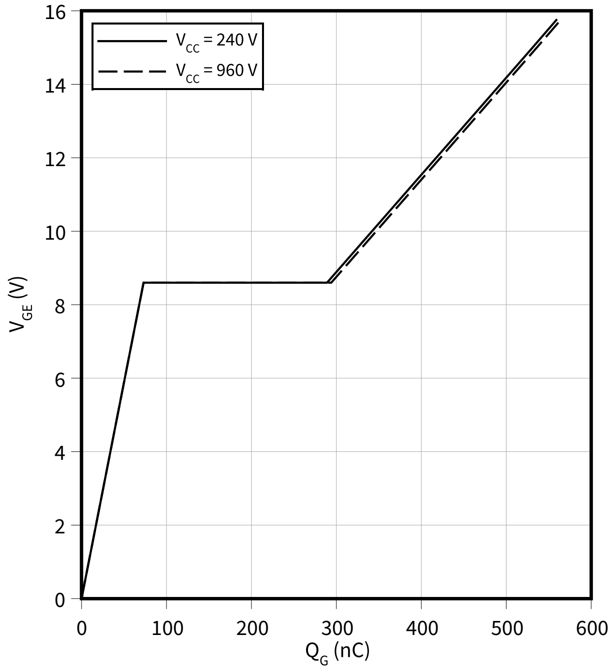
I_C = 75 A, $T_{vj} \geq$ 25 °C, V_{GE} = 0/15 V, R_G = 8 Ω



Typical gate charge

$V_{GE} = f(Q_G)$

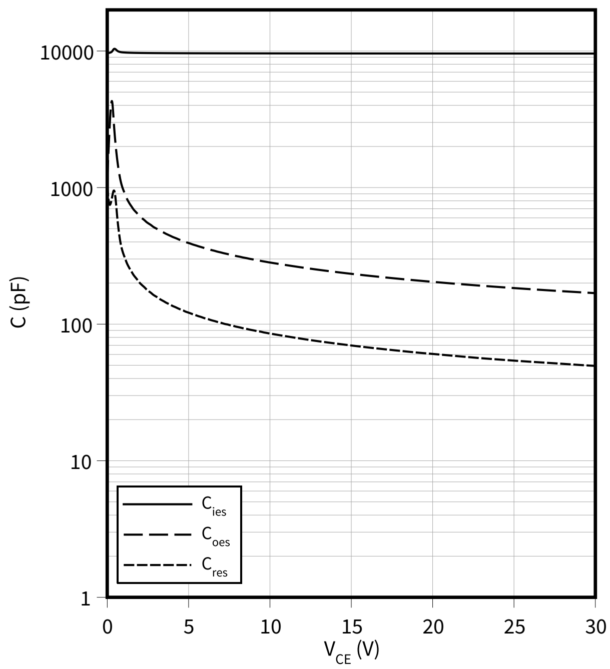
I_C = 75 A



Typical capacitance as a function of collector-emitter voltage

$C = f(V_{CE})$

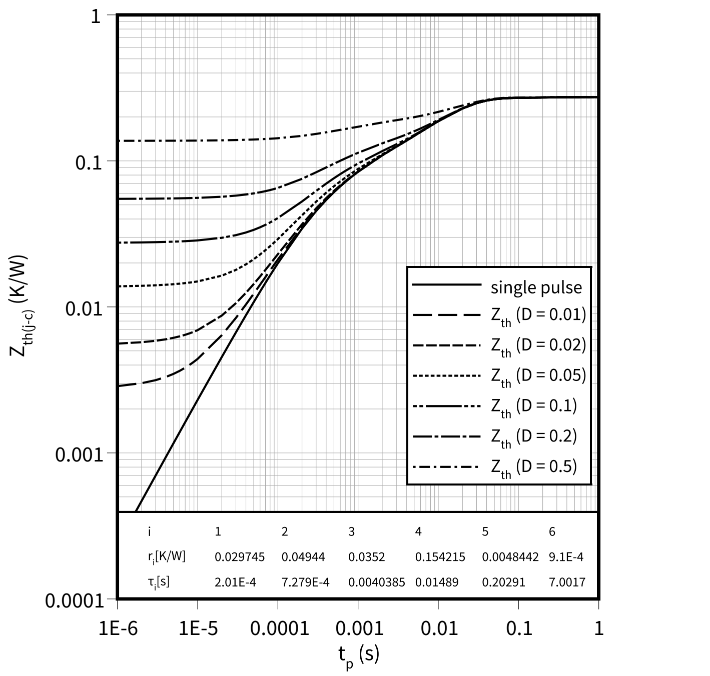
f = 100 kHz, V_{GE} = 0 V



IGBT transient thermal impedance as a function of pulse width

$Z_{th(j-c)} = f(t_p)$

$D = t_p/T$

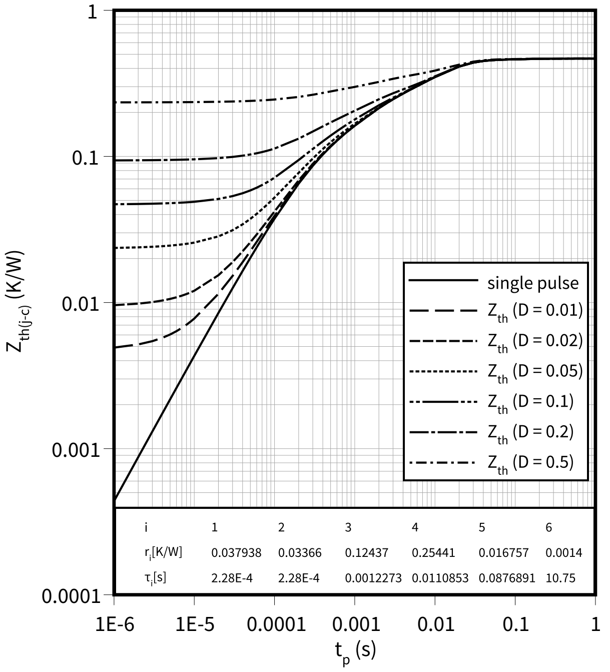


i	1	2	3	4	5	6
r_i[K/W]	0.029745	0.04944	0.0352	0.154215	0.0048442	9.1E-4
τ_i[s]	2.01E-4	7.279E-4	0.0040385	0.01489	0.20291	7.0017

Diode transient thermal impedance as a function of pulse width

$Z_{th(j-c)} = f(t_p)$

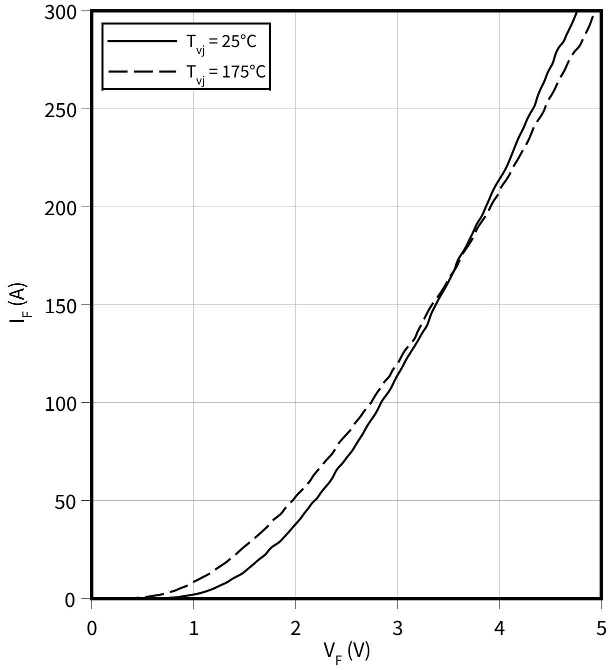
$D = t_p/T$



i	1	2	3	4	5	6
r_i[K/W]	0.037938	0.03366	0.12437	0.25441	0.016757	0.0014
τ_i[s]	2.28E-4	2.28E-4	0.0012273	0.0110853	0.0876891	10.75

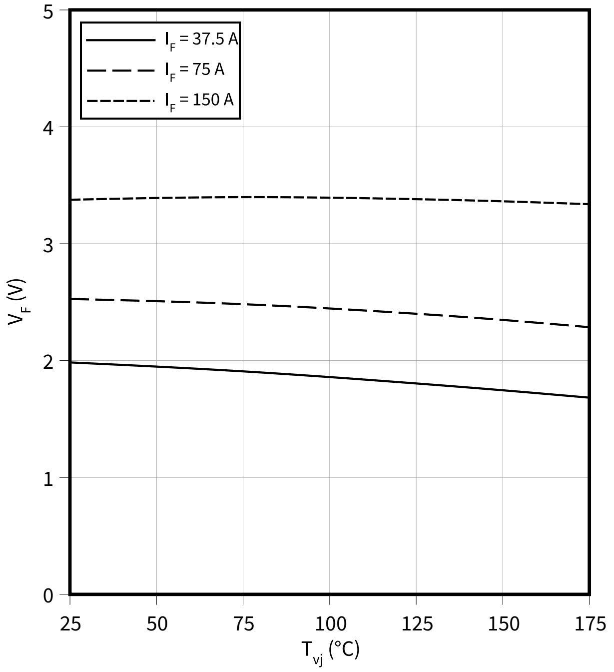
Typical diode forward current as a function of forward voltage

$I_F = f(V_F)$



Typical diode forward voltage as a function of junction temperature

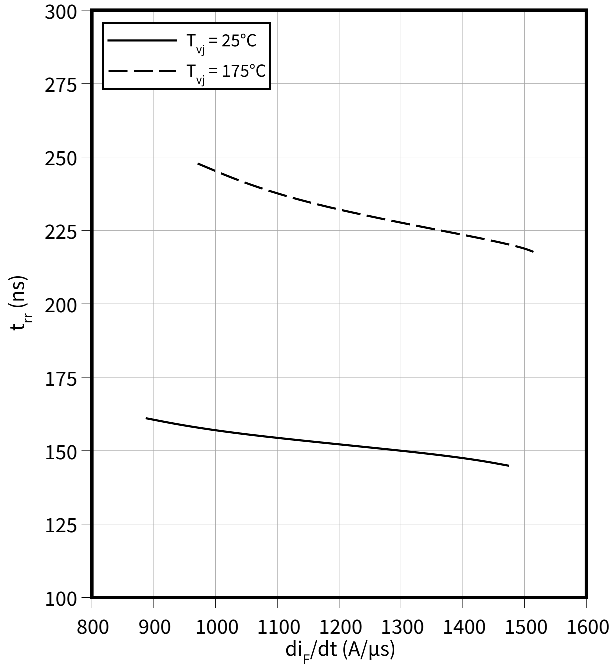
$V_F = f(T_{vj})$



Typical reverse recovery time as a function of diode current slope

$t_{rr} = f(di_F/dt)$

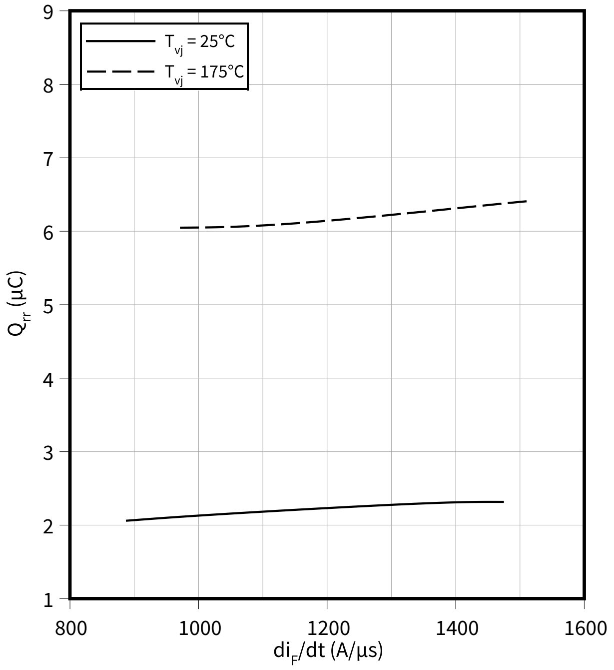
$V_R = 600$ V, $I_F = 75$ A



Typical reverse recovery charge as a function of diode current slope

$Q_{rr} = f(di_F/dt)$

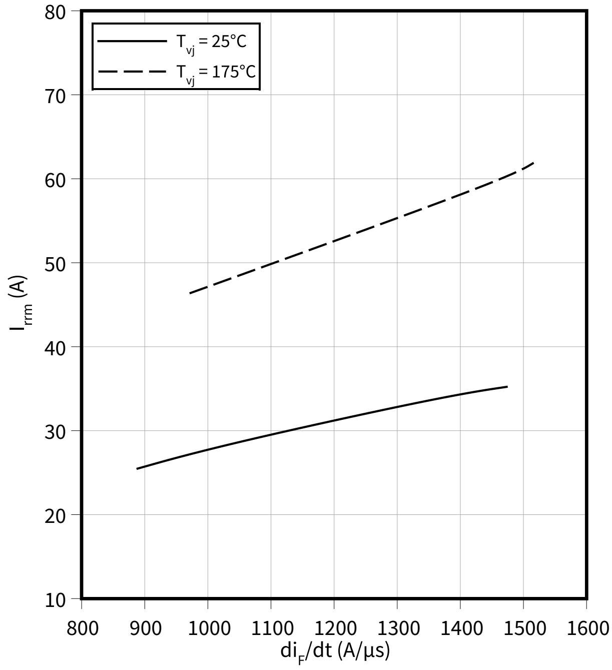
$V_R = 600$ V, $I_F = 75$ A



Typical reverse recovery current as a function of diode current slope

$I_{rrm} = f(di_F/dt)$

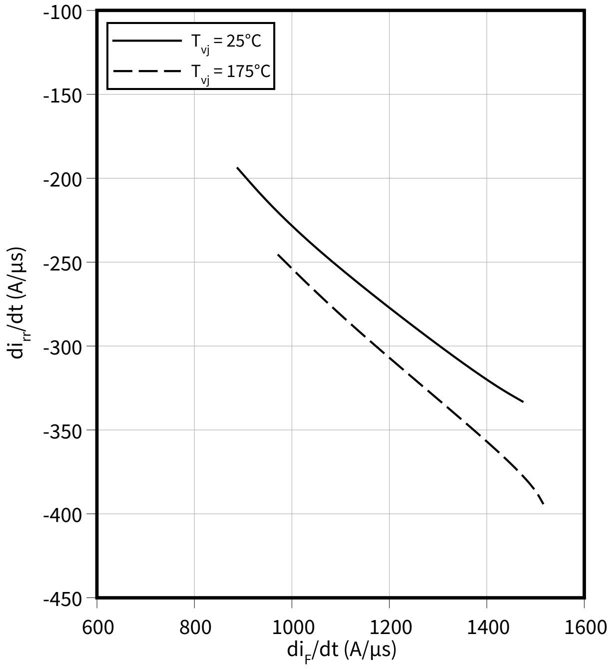
$V_R = 600$ V, $I_F = 75$ A



Typical diode peak rate of fall of reverse recovery current as a function of diode current slope

$di_{rr}/dt = f(di_F/dt)$

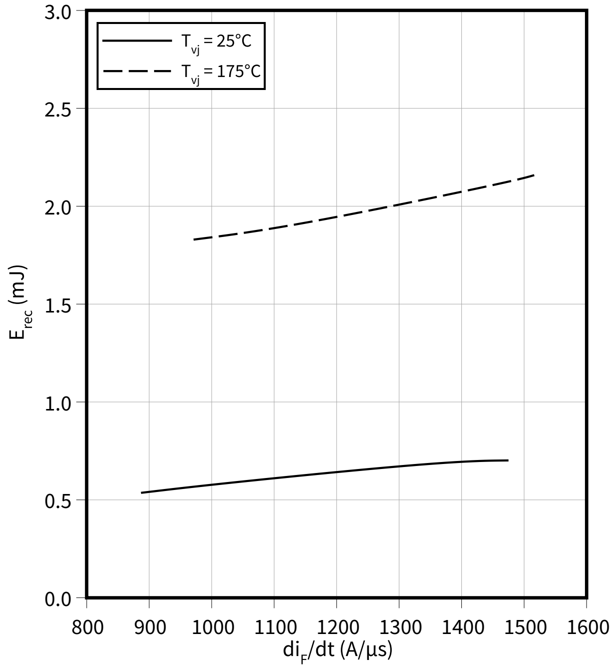
$V_R = 600$ V, $I_F = 75$ A



Typical reverse energy losses as a function of diode current slope

$E_{rec} = f(di_F/dt)$

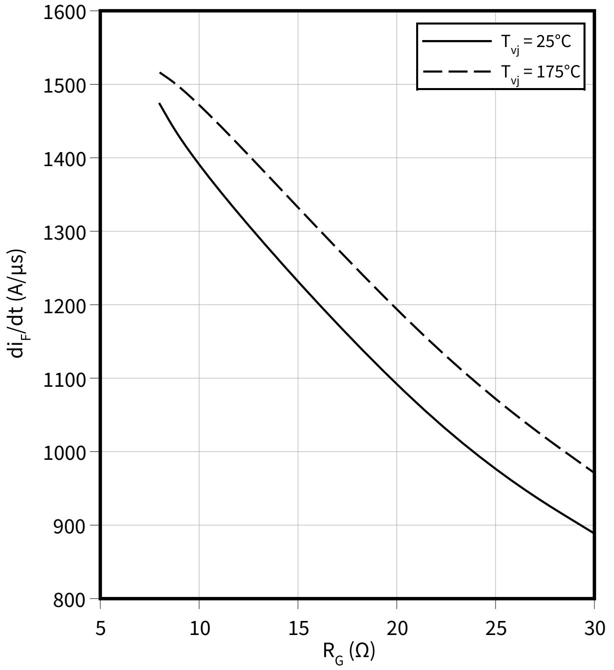
$V_R = 600$ V, $I_F = 75$ A



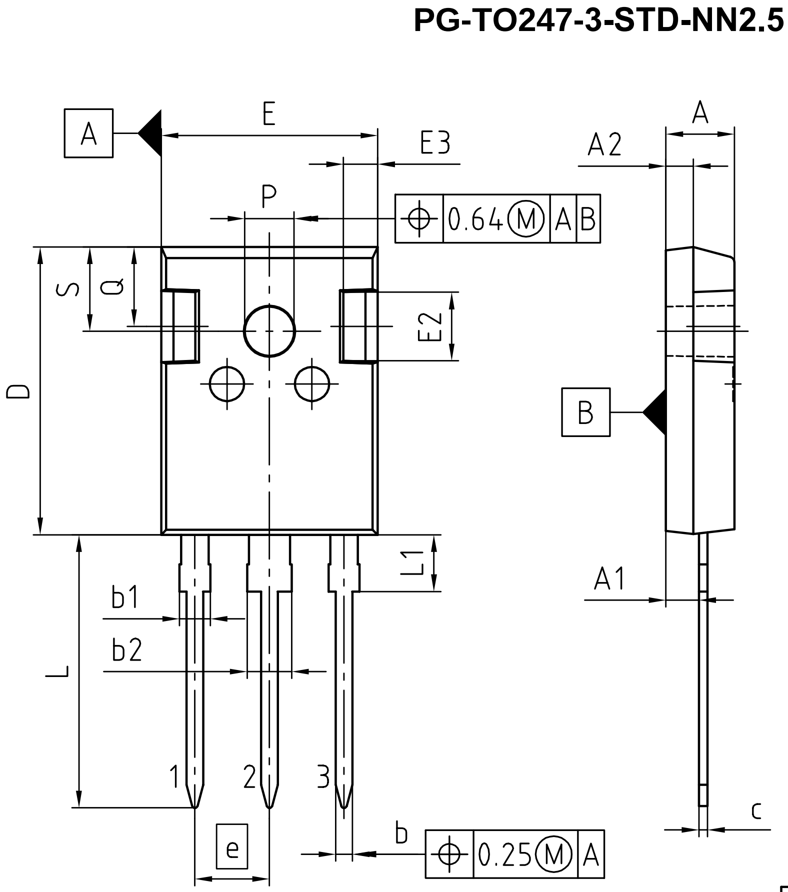
Typical diode current slope as a function of gate resistor

$di_F/dt = f(R_G)$

$V_R = 600$ V, $I_F = 75$ A



5 Package outlines



PACKAGE - GROUP NUMBER:	PG-TO247-3-U06	
DIMENSIONS	MILLIMETERS	
	MIN.	MAX.
A	4.83	5.21
A1	2.27	2.54
A2	1.85	2.16
b	1.07	1.33
b1	1.90	2.41
b2	2.87	3.38
c	0.55	0.68
D	20.80	21.10
D1	16.25	17.65
D2	0.95	1.35
E	15.70	16.13
E1	13.10	14.15
E2	3.68	5.10
E3	1.00	2.60
e	5.44	
N	3	
L	19.80	20.32
L1	4.10	4.47
øP	3.50	3.70
Q	5.49	6.00
S	6.04	6.30

NOTE:
DIMENSIONS DO NOT INCLUDE MOLDFLASH; PROTRUSION OR GATE BURRS

Figure 1

6 Testing conditions

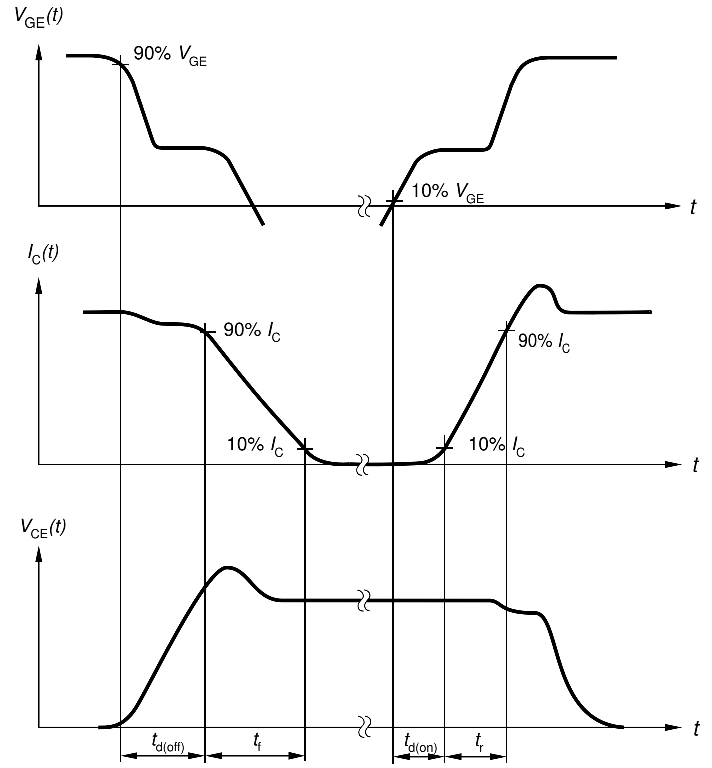


Figure A. **Definition of switching times**

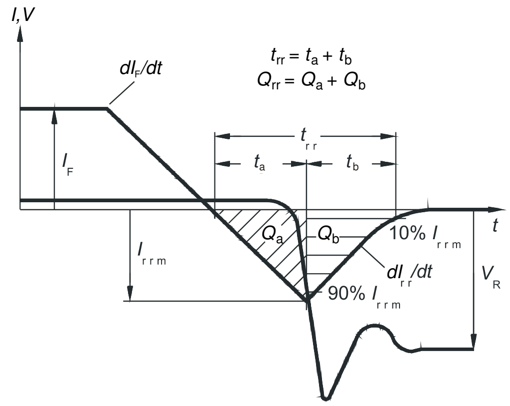


Figure C. **Definition of diode switching characteristics**

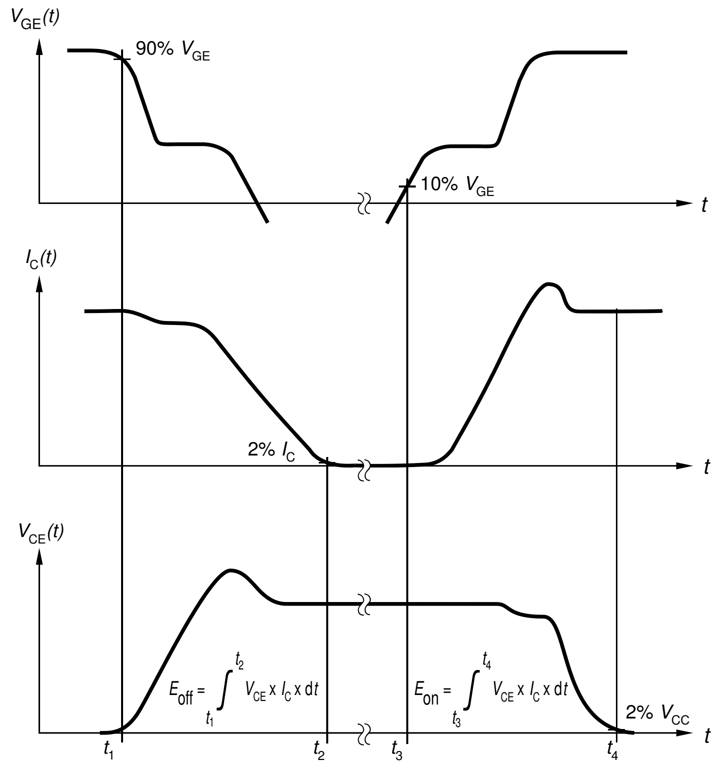


Figure B. **Definition of switching losses**

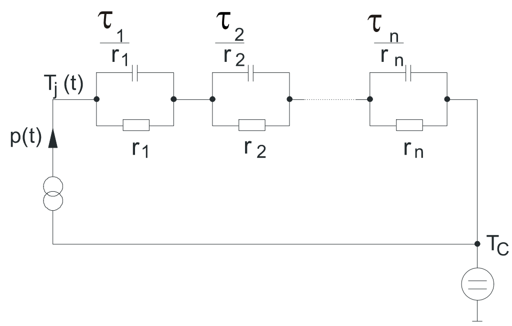


Figure D. **Thermal equivalent circuit**

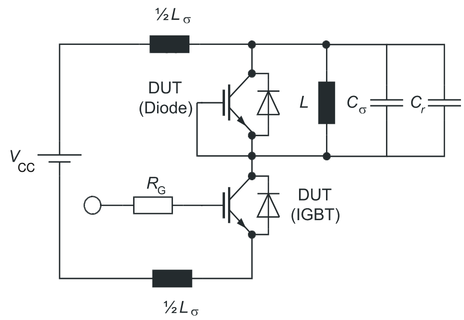


Figure E. **Dynamic test circuit**
Parasitic inductance L_{σ},
parasitic capacitor C_{σ},
relief capacitor C_r,
(only for ZVT switching)

Figure 2

Revision history

Document revision	Date of release	Description of changes
0.10	2022-05-02	Target datasheet
0.20	2022-05-19	Editorial changes
0.30	2022-06-01	Editorial changes
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